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## ESD3V3D5 Thru ESD12VD5

### Features

- For sensitive ESD protection
  - Excellent clamping capability
  - Low leakage
  - ESD rating of class 3(>16KV)per Human Body Mode
  - For space saving application
  - Fast response ,response time less than 1ns.
- Epoxy meets UL 94 V-0 flammability rating  
Moisture Sensitivity Level 1

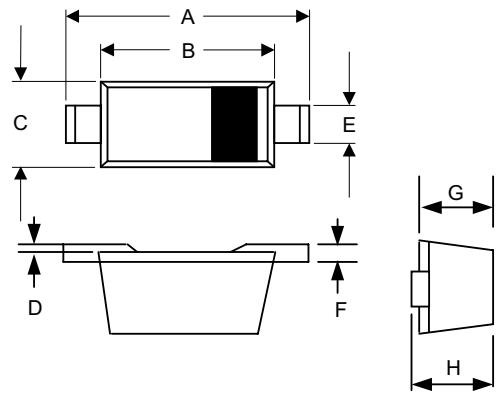
**3.3V~12Volts  
ESD Protection  
Devices**

### Maximum Ratings

- Operating Junction &StorageTemperature: -55°C to +150°C
- Maximum Thermal Resistance: 625°C/W Junction To Ambient

Parameter	Symbol	Limits	unit
IEC61000-4-2(ESD) Air Contact		±30 ±30	KV
ESD Voltage per human body mode per machine mode		16 400	KV V
Power Dissipation	Pd	200	mw

SOD523

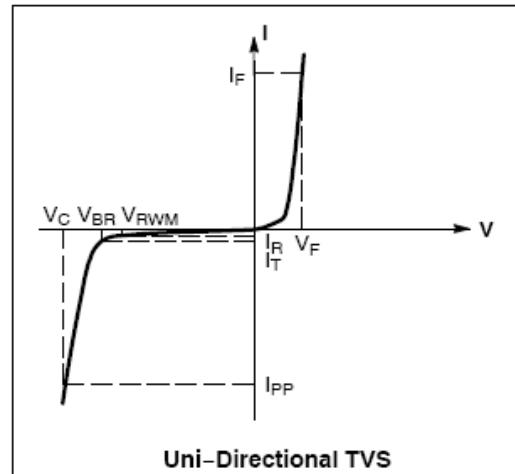


DIM	DIMENSIONS				NOTE	
	INCHES		MM			
	MIN	MAX	MIN	MAX		
A	.059	.067	1.50	1.70		
B	.043	.051	1.10	1.30		
C	.030	.033	0.75	0.85		
D	.001	.003	0.01	0.07		
E	.010	.014	0.25	0.35		
F	.003	.006	0.08	0.15		
G	.020	.028	0.50	0.70		
H	.020	.031	0.51	0.77		



### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter
$I_{PP}$	Maximum Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Working Peak Reverse Voltage
$I_R$	Maximum Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current
$I_F$	Forward Current
$V_F$	Forward Voltage @ $I_F$
$P_{pk}$	Peak Power Dissipation
C	Max. Capacitance @ $V_R=0$ and $f=1\text{MHz}$



### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted, $V_F = 0.9 \text{ V Max.}$ @ $I_F = 10\text{mA}$ for all types)

Device*	Device Marking	$V_{RWM} (\text{V})$	$I_R (\mu\text{A})$ @ $V_{RWM}$	$V_{BR} (\text{V})$ @ $I_T$ (Note 2)	$I_T$	$V_C$ @ $I_{PP^+} = 5 \text{ A}$	$I_{PP} (\text{A})^+$	$V_c (\text{V})$ @ Max $I_{PP^+}$	$P_{pk^+} (\text{W})$	C (pF)
		Max	Max	Min	mA					
ESD3V3D5	ZE	3.3	0.08	5.0	1.0	9.4	11.2	14.1	158	105
ESD5V0D5	ZF	5.0	0.08	6.2	1.0	11.6	9.4	18.6	174	80
ESD7V0D5	ZH	7.0	0.03	7.5	1.0	13.5	8.8	22.7	200	65
ESD12VD5	ZM	12	0.02	14.1	1.0	23	9.6	29	240	55

+Surge current waveform per Figure 1.

2.  $V_{BR}$  is measured with a pulse test current  $I_T$  at an ambient temperature of  $25^\circ\text{C}$ .

### TYPICAL CHARACTERISTICS

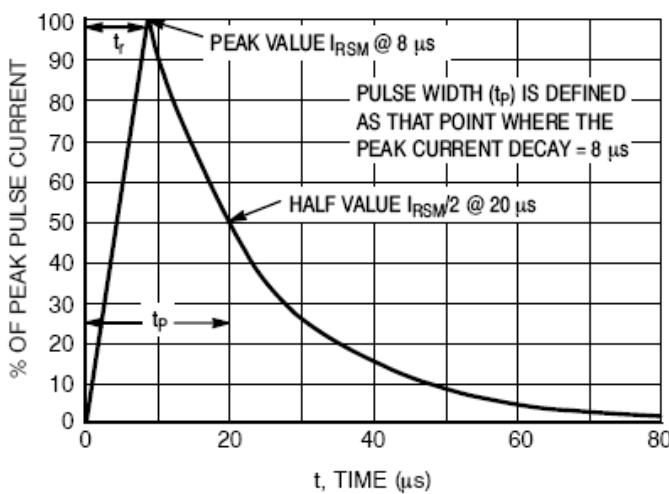


Figure 1.  $8 \times 20 \mu\text{s}$  Pulse Waveform